



General Description:

- (1) Chip Dimension
 Chip Size= 8 mil x 10 mil (205um x 255um)
 Chip Thickness = 90±10 μm
 P/N Bonding Pad = 85±5 μm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics(Ta=RT)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Luminous Intensity	I _v	-	9	-	mw	I _F =20mA
Forward Voltage	V _F	-	3.8	-	V	I _F =20mA
Dominant Wavelength	λ _D	-	400	-	nm	I _F =20mA
Reverse Current	I _R	0	-	2	μA	V _R =-5V

Features:

- (1) High Luminous Intensity
- (2) Long Operation Life
- (3) High Current; Pulse Operation
- (4) Indoor/Outdoor Applications

Notes:

1. Dominant wavelength includes an error of ± 1nm
2. Luminous intensity includes an error of ±10%
3. Luminous intensity is measured on bare chip
4. InGaN LED is sensitive to ESD

